

Title (en)

Method of operating semiconductor device including variable resistance device

Title (de)

Verfahren zum Betreiben einer Halbleitervorrichtung mit verstellbarer Widerstandsvorrichtung

Title (fr)

Procédé de fonctionnement d'un dispositif semi-conducteur incluant un dispositif à résistance variable

Publication

EP 2562763 A2 20130227 (EN)

Application

EP 12180682 A 20120816

Priority

KR 20110083579 A 20110822

Abstract (en)

According to an example embodiment, a method of operating a semiconductor device having a variable resistance device includes: applying a first voltage to the variable resistance device to change a resistance value of the variable resistance device from a first resistance value to a second resistance value that is different from the first resistance value; sensing a first current flowing through the variable resistance device to which the first voltage is applied; determining a second voltage used for changing the variable resistance device from the second resistance value to the first resistance value, based on a dispersion of the sensed first current; and applying the determined second voltage to the variable resistance device.

IPC 8 full level

G11C 13/00 (2006.01); **G11C 11/56** (2006.01)

CPC (source: EP KR)

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Cited by

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Designated contracting state (EPC)

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Designated extension state (EPC)

BA ME

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EP 2562763 A2 20130227; **EP 2562763 A3 20141112**; **EP 2562763 B1 20191002**; CN 102956263 A 20130306; JP 2013045496 A 20130304; JP 5978063 B2 20160824; KR 20130021198 A 20130305

DOCDB simple family (application)

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